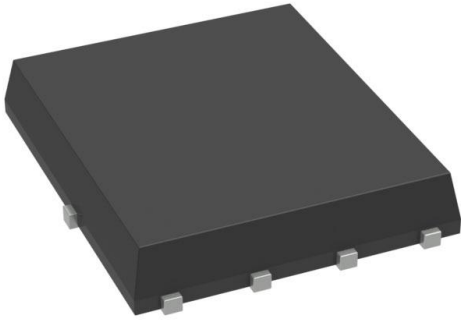


FDMS86581 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FDMS86581-DG
Manufacturer	onsemi
Manufacturer Product Number	FDMS86581
Description	MOSFET N-CH 60V 30A 8PQFN
Detailed Description	N-Channel 60 V 30A (Tc) 50W (Tj) Surface Mount 8-PQFN (5x6)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

FDMS86581

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

8-PQFN (5x6)

Base Product Number:

FDMS86581

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

30A (Tc)

Rds On (Max) @ Id, Vgs:

15mOhm @ 30A, 10V

Gate Charge (Qg) (Max) @ Vgs:

19 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

881 pF @ 30 V

Power Dissipation (Max):

50W (Tj)

Mounting Type:

Surface Mount

Package / Case:

8-PowerTDFN

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – N-Channel, POWERTRENCH®

60 V, 30 A, 15 mΩ

FDMS86581

Features

- Typical $R_{DS(on)}$ = 12.5 mΩ at $V_{GS} = 10$ V, $I_D = 30$ A
- Typical $Q_{G(tot)}$ = 13 nC at $V_{GS} = 10$ V, $I_D = 25$ A
- UIS Capability
- RoHS Compliant

Applications

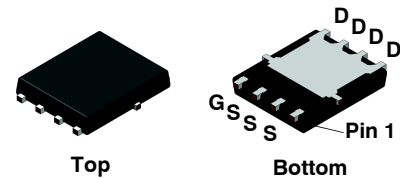
- DC–DC Power Supplies
- AC–DC Power Supplies
- Motor Control
- Load Switching

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Drain Current – Continuous ($V_{GS} = 10$) $T_C = 25^\circ\text{C}$ (Note 1)	30	A
	Pulsed Drain Current, $T_C = 25^\circ\text{C}$	See Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	13.5	mJ
P_D	Power Dissipation	50	W
	Derate Above 25°C	0.33	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	–55 to +175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	50	$^\circ\text{C}/\text{W}$

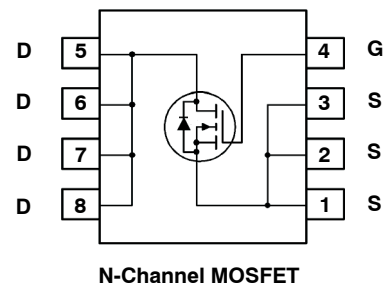
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting $T_J = 25^\circ\text{C}$, $L = 40$ μH, $I_{AS} = 26$ A, $V_{DD} = 60$ V during inductor charging and $V_{DD} = 0$ V during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2 oz copper.



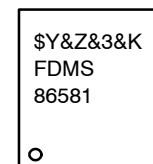
Power 56
(PQFN8 5x6)
CASE 483AE

ELECTRICAL CONNECTION



N-Channel MOSFET

MARKING DIAGRAM



\$Y = onsemi Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 FDMS86581 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

FDMS86581

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
--------	-----------	-----------------	-----	------	------	-------

OFF CHARACTERISTICS

B_{VDSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	60	-	-	V	
I_{DSS}	Drain-to-Source Leakage Current	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$	-	-	1	A
			$T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	mA
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	2.0	2.7	4.0	V	
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 30 \text{ A}$, $V_{GS} = 10 \text{ V}$	$T_J = 25^\circ\text{C}$	-	12.5	15.0	$\text{m}\Omega$
			$T_J = 175^\circ\text{C}$ (Note 4)	-	25.1	30.1	$\text{m}\Omega$

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	881	-	pF
C_{oss}	Output Capacitance		-	281	-	pF
C_{rss}	Reverse Transfer Capacitance		-	15	-	pF
R_G	Gate Resistance	$f = 1 \text{ MHz}$	-	3.1	-	Ω
$Q_{g(ToT)}$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10 \text{ V}$, $V_{DD} = 30 \text{ V}$, $I_D = 25 \text{ A}$	-	13	19	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2 \text{ V}$, $V_{DD} = 30 \text{ V}$, $I_D = 25 \text{ A}$	-	2	-	nC
Q_{gs}	Gate-to-Source Gate Charge	$V_{DD} = 30 \text{ V}$, $I_D = 25 \text{ A}$	-	4	-	nC
Q_{gd}	Gate-to-Drain "Miller" Charge		-	3	-	nC

SWITCHING CHARACTERISTICS

t_{on}	Turn-On Time	$V_{DD} = 30 \text{ V}$, $I_D = 30 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$	-	-	20	ns
$t_{d(on)}$	Turn-On Delay		-	9	-	ns
t_r	Rise Time		-	5	-	ns
$t_{d(off)}$	Turn-Off Delay		-	15	-	ns
t_f	Fall Time		-	4	-	ns
t_{off}	Turn-Off Time		-	-	28	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source-to-Drain Diode Voltage	$I_{SD} = 30 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	-	1.25	V
		$I_{SD} = 15 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	-	1.2	V
t_{rr}	Reverse-Recovery Time	$I_F = 30 \text{ A}$, $di_{SD}/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 48 \text{ V}$	-	37	55	ns
Q_{rr}	Reverse Recovery Charge		-	22	33	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production.

FDMS86581

TYPICAL CHARACTERISTICS

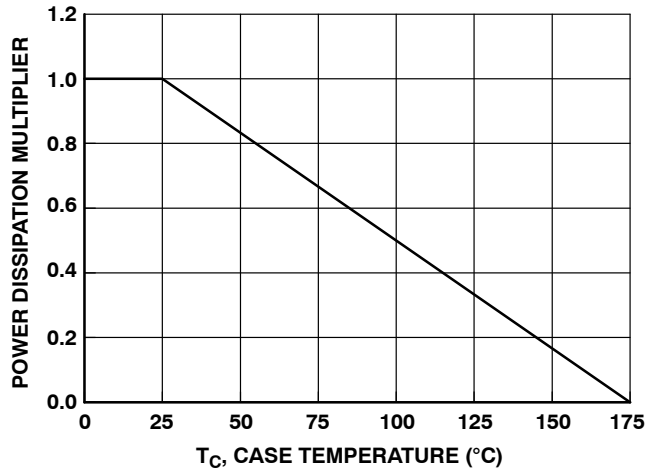


Figure 1. Normalized Power Dissipation vs. Case Temperature

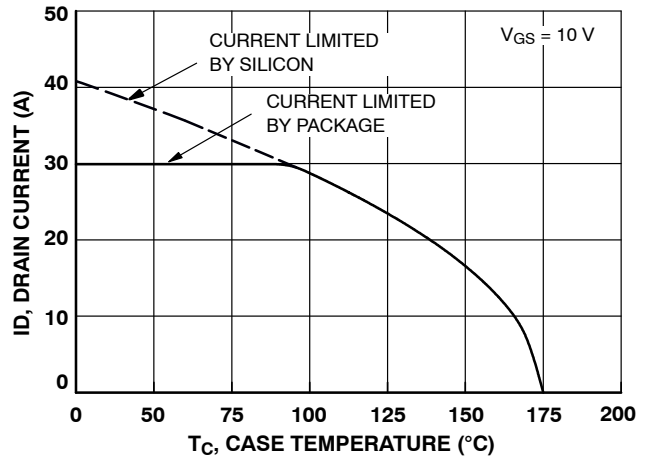


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

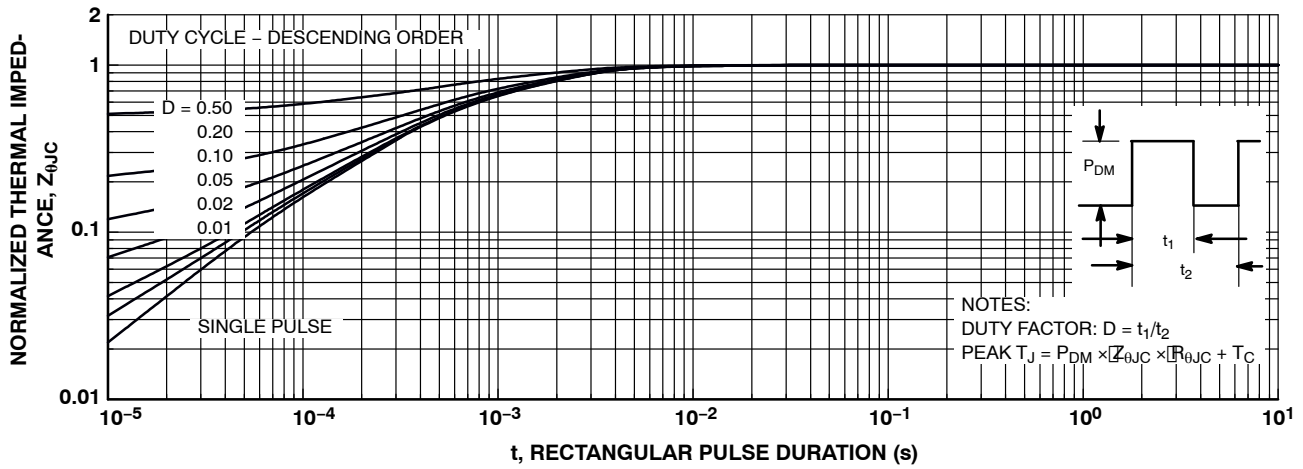


Figure 3. Normalized Maximum Transient Thermal Impedance

FDMS86581

TYPICAL CHARACTERISTICS (continued)

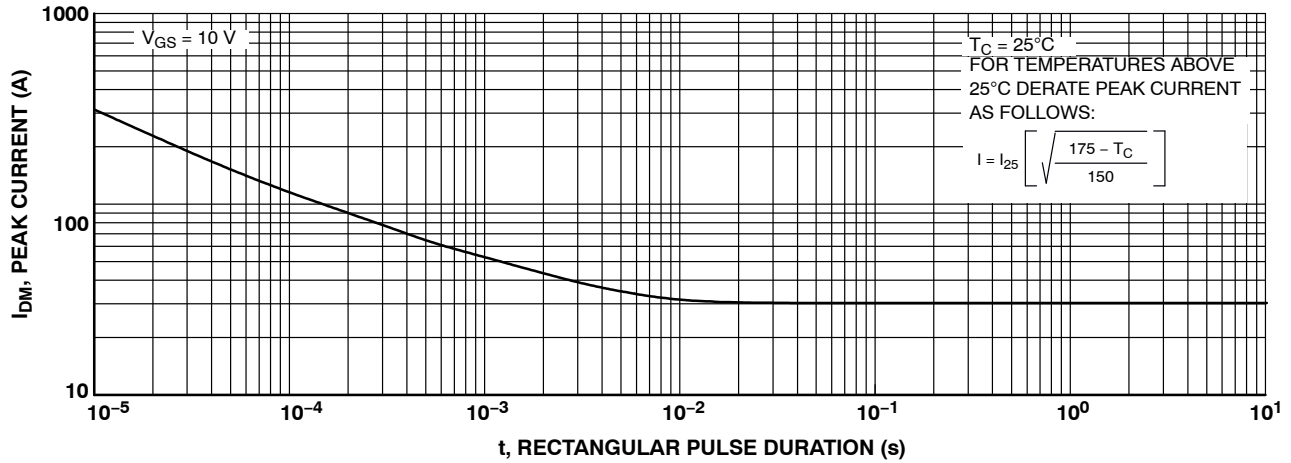


Figure 4. Peak Current Capability

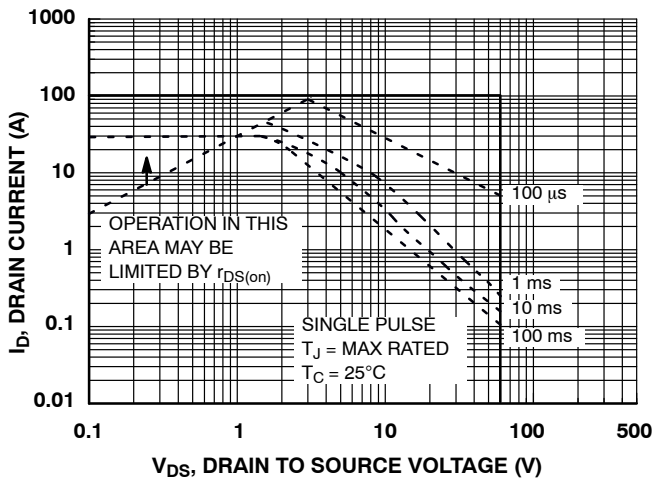
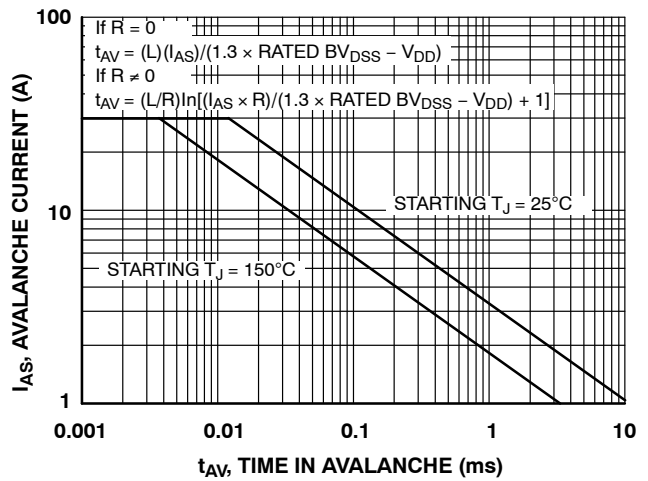


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to onsemi Application Notes [AN7514](#) and [AN7515](#).

Figure 6. Unclamped Inductive Switching Capability

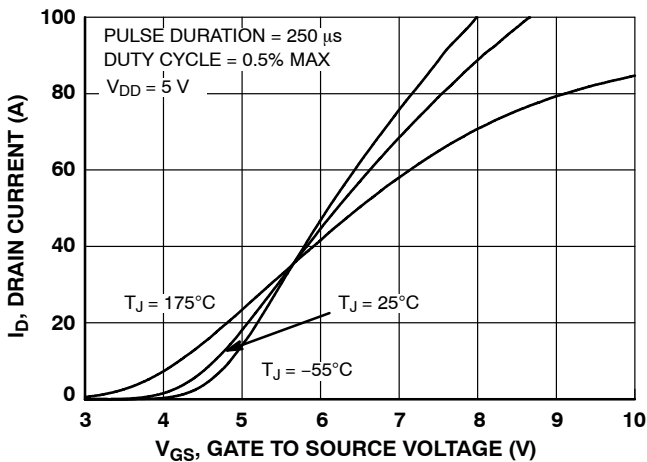


Figure 7. Transfer Characteristics

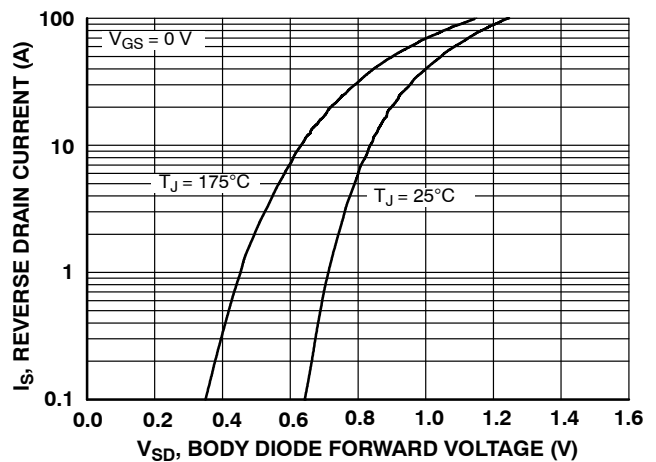


Figure 8. Forward Diode Characteristics

FDMS86581

TYPICAL CHARACTERISTICS (CONTINUED)

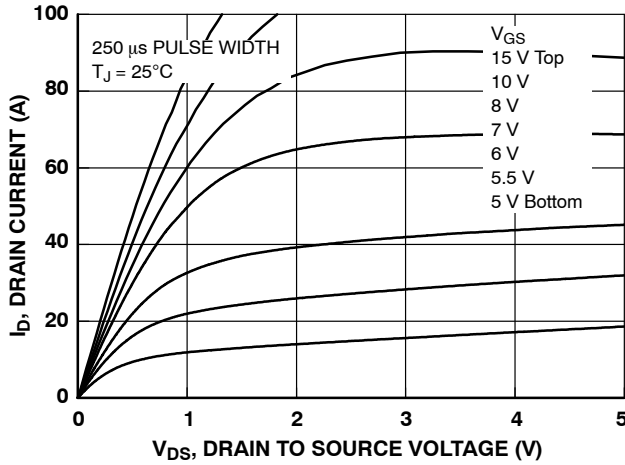


Figure 9. Saturation Characteristics

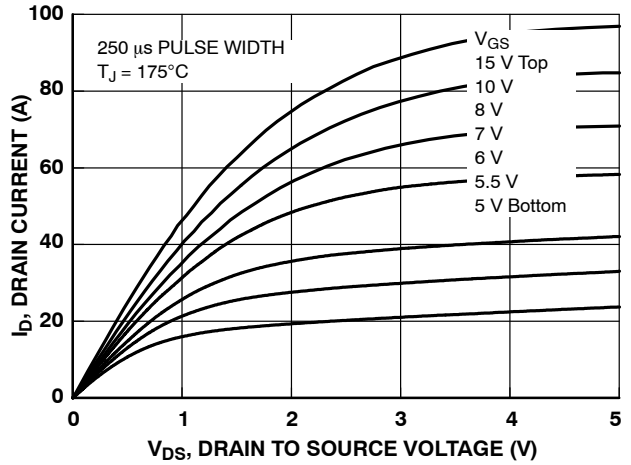


Figure 10. Saturation Characteristics

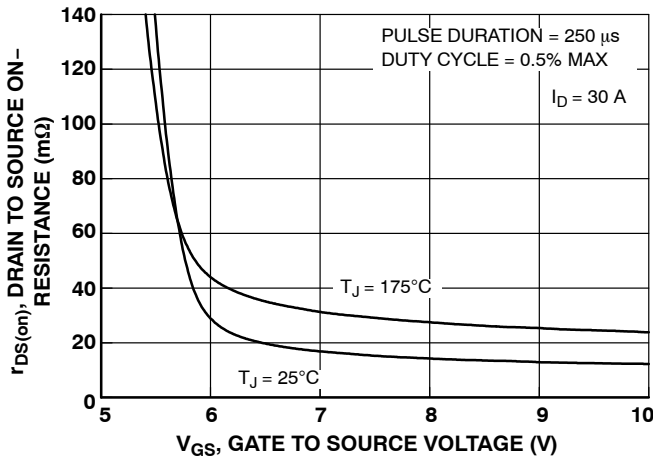


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

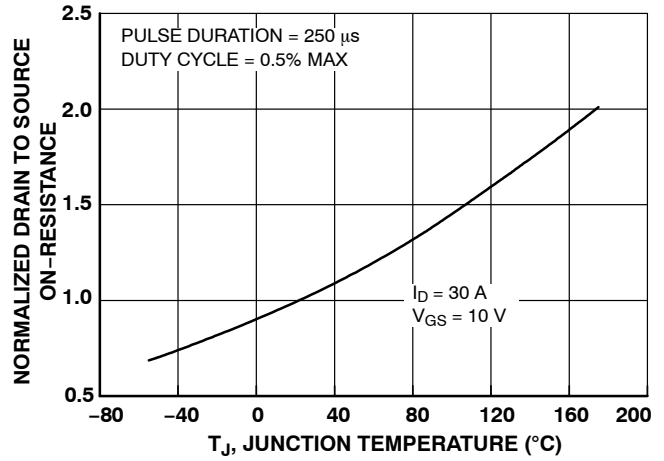


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

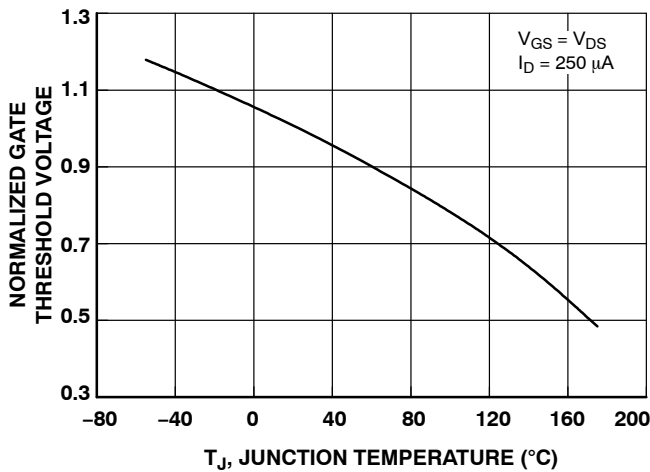


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

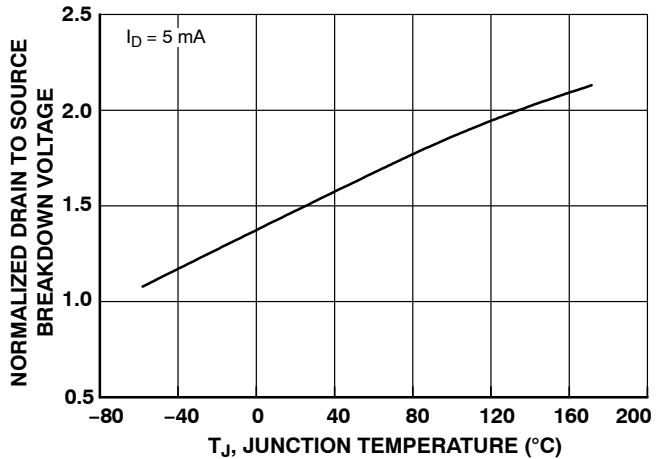


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

FDMS86581

TYPICAL CHARACTERISTICS (continued)

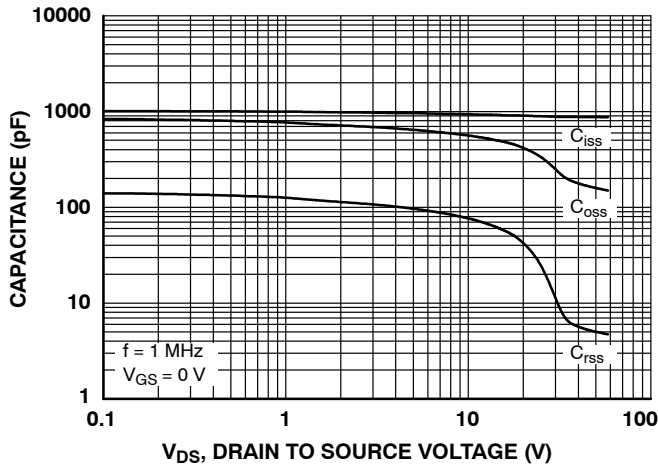


Figure 15. Capacitance vs. Drain to Source Voltage

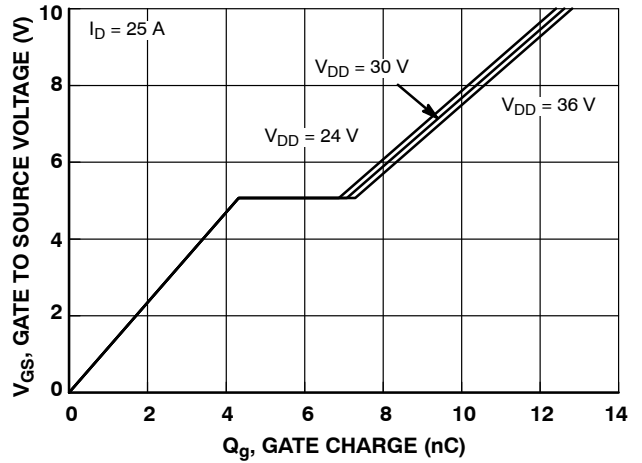


Figure 16. Gate Charge vs. Gate to Source Voltage

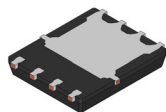
PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Shipping [†]
FDMS86581	FDMS86581	Power 56	3000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

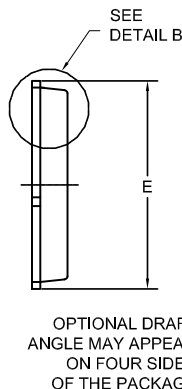
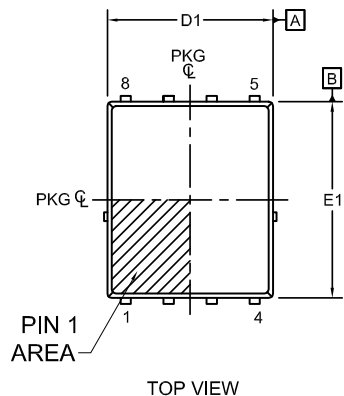


**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



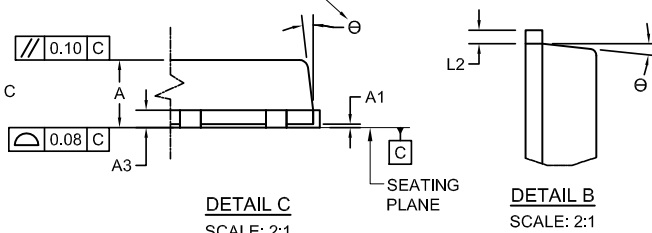
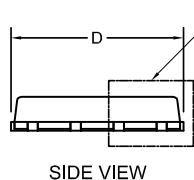
**PQFN8 5X6, 1.27P
CASE 483AE
ISSUE C**

DATE 21 JAN 2022

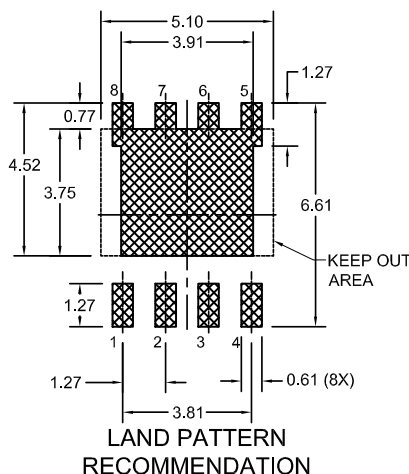
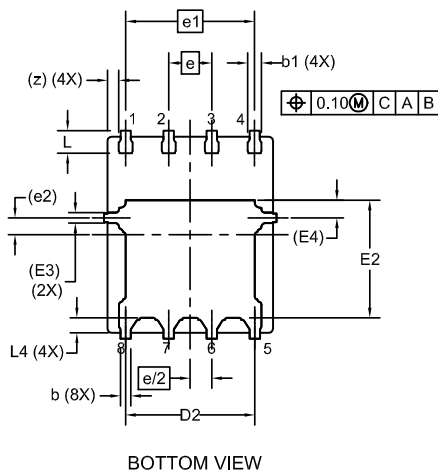


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.21	0.31	0.41
b1	0.31	0.41	0.51
A3	0.15	0.25	0.35
D	4.90	5.00	5.20
D1	4.80	4.90	5.00
D2	3.61	3.82	3.96
E	5.90	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.78
E3	0.30 REF		
E4	0.52 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
e2	0.50 REF		
L	0.51	0.66	0.76
L2	0.05	0.18	0.30
L4	0.34	0.44	0.54
z	0.34 REF		
θ	0°	-	12°



*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	PQFN8 5X6, 1.27P	PAGE 1 OF 1

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